

# 256K (32K x 8) Static RAM

## Features

- High speed: 55 ns and 70 ns
- Voltage range: 4.5V–5.5V operation
- Low active power (70 ns, LL version)  
— 275 mW (max.)
- Low standby power (70 ns, LL version)  
— 28  $\mu$ W (max.)
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- TTL-compatible inputs and outputs
- Automatic power-down when deselected
- CMOS for optimum speed/power
- Package available in a standard 450-mil-wide (300-mil body width) 28-lead narrow SOIC, 28-lead TSOP-1, 28-lead reverse TSOP-1, and 600-mil 28-lead PDIP packages

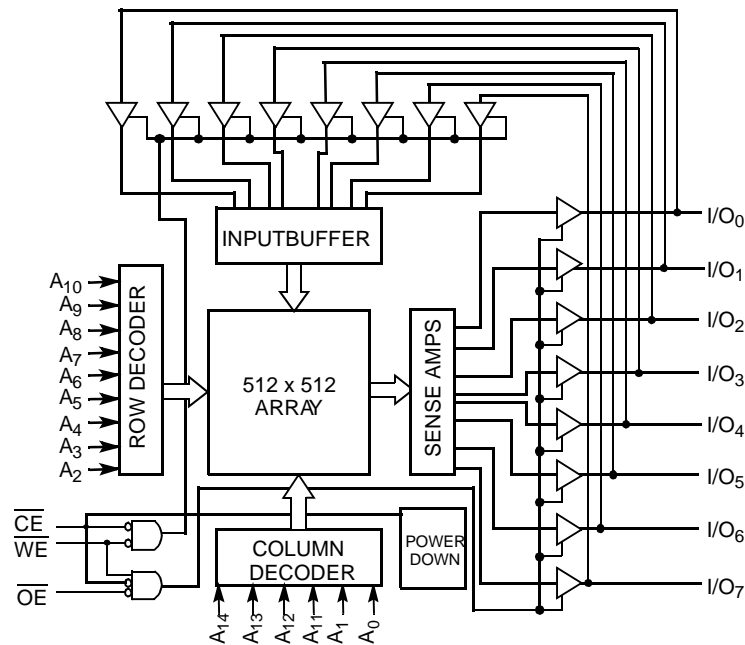
## Functional Description<sup>[1]</sup>

The CY62256 is a high-performance CMOS static RAM organized as 32K words by 8 bits. Easy memory expansion is provided by an active LOW chip enable ( $\overline{CE}$ ) and active LOW output enable ( $\overline{OE}$ ) and three-state drivers. This device has an automatic power-down feature, reducing the power consumption by 99.9% when deselected.

An active LOW write enable signal ( $\overline{WE}$ ) controls the writing/reading operation of the memory. When  $\overline{CE}$  and  $\overline{WE}$  inputs are both LOW, data on the eight data input/output pins ( $I/O_0$  through  $I/O_7$ ) is written into the memory location addressed by the address present on the address pins ( $A_0$  through  $A_{14}$ ). Reading the device is accomplished by selecting the device and enabling the outputs,  $\overline{CE}$  and  $\overline{OE}$  active LOW, while  $\overline{WE}$  remains inactive or HIGH. Under these conditions, the contents of the location addressed by the information on address pins are present on the eight data input/output pins.

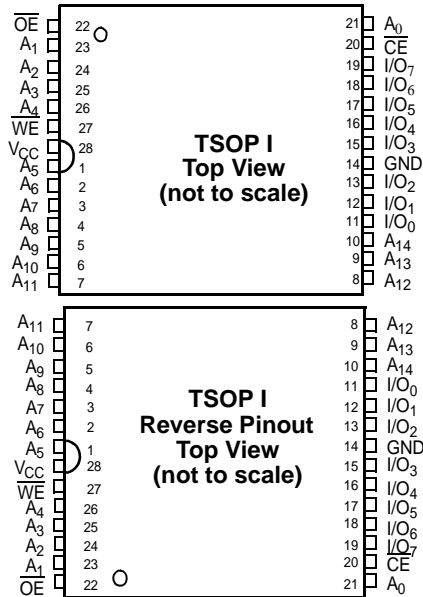
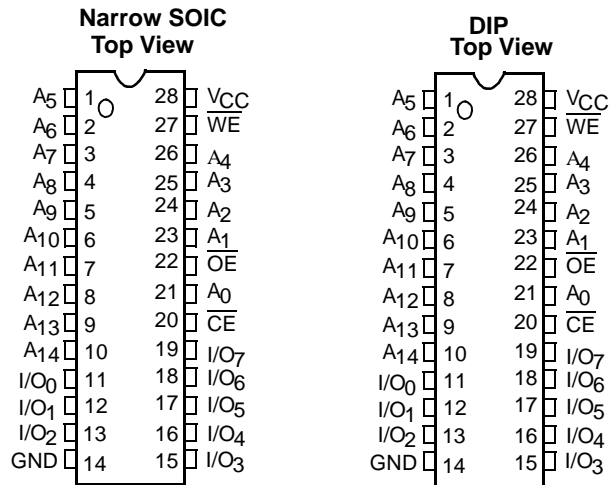
The input/output pins remain in a high-impedance state unless the chip is selected, outputs are enabled, and write enable ( $\overline{WE}$ ) is HIGH.

## Logic Block Diagram



### Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

**Pin Configurations**

**Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... -65°C to +150°C

Ambient Temperature with Power Applied ..... 0°C to +70°C

Supply Voltage to Ground Potential (Pin 28 to Pin 14) ..... -0.5V to +7.0V

DC Voltage Applied to Outputs in High-Z State<sup>[2]</sup> ..... -0.5V to  $V_{CC} + 0.5V$

DC Input Voltage<sup>[2]</sup> ..... -0.5V to  $V_{CC} + 0.5V$

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... > 200 mA

**Operating Range**

Range	Ambient Temperature	$V_{CC}$
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	5V ± 10%

**Electrical Characteristics** Over the Operating Range

Parameter	Description	Test Conditions	CY62256-55			CY62256-70			Unit
			Min.	Typ. <sup>[3]</sup>	Max.	Min.	Typ. <sup>[3]</sup>	Max.	
$V_{OH}$	Output HIGH Voltage	$V_{CC} = \text{Min.}, I_{OH} = -1.0 \text{ mA}$	2.4			2.4			V
$V_{OL}$	Output LOW Voltage	$V_{CC} = \text{Min.}, I_{OL} = 2.1 \text{ mA}$			0.4			0.4	V
$V_{IH}$	Input HIGH Voltage		2.2		$V_{CC} + 0.5V$	2.2		$V_{CC} + 0.5V$	V
$V_{IL}$	Input LOW Voltage		-0.5		0.8	-0.5		0.8	V
$I_{IX}$	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-0.5		+0.5	-0.5		+0.5	μA
$I_{OZ}$	Output Leakage Current	$GND \leq V_O \leq V_{CC}$ , Output Disabled	-0.5		+0.5	-0.5		+0.5	μA
$I_{CC}$	$V_{CC}$ Operating Supply Current	$V_{CC} = \text{Max.}, I_{OUT} = 0 \text{ mA}, f = f_{MAX} = 1/t_{RC}$		28	55	28	55	mA	
			L	25	50	25	50	mA	
			LL	25	50	25	50	mA	
$I_{SB1}$	Automatic CE Power-down Current—TTL Inputs	Max. $V_{CC}$ , $CE \geq V_{IH}$ , $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$ , $f = f_{MAX}$		0.5	2	0.5	2	mA	
			L	0.4	0.6	0.4	0.6	mA	
			LL	0.3	0.5	0.3	0.5	mA	

**Notes:**

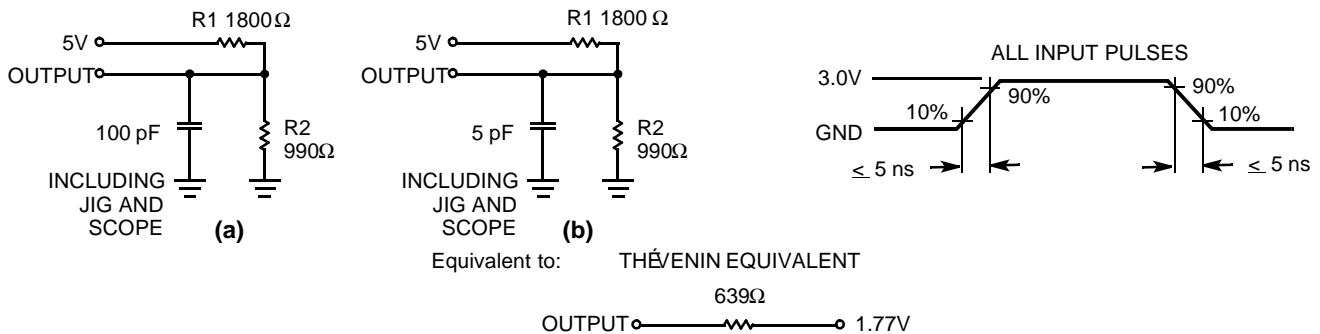
- $V_{IL}$  (min.) = -2.0V for pulse durations of less than 20 ns.
- Typical specifications are the mean values measured over a large sample size across normal production process variations and are taken at nominal conditions ( $T_A = 25^\circ\text{C}$ ,  $V_{CC}$ ). Parameters are guaranteed by design and characterization, and not 100% tested.

**Electrical Characteristics** Over the Operating Range (continued)

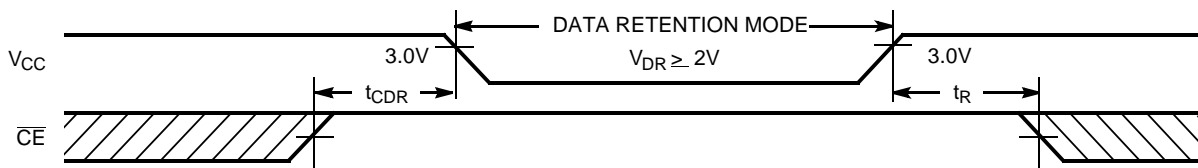
Parameter	Description	Test Conditions	CY62256-55			CY62256-70			Unit	
			Min.	Typ. <sup>[3]</sup>	Max.	Min.	Typ. <sup>[3]</sup>	Max.		
$I_{SB2}$	Automatic CE Power-down Current—CMOS Inputs	Max. $V_{CC}$ , $CE \geq V_{CC} - 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ , or $V_{IN} \leq 0.3V$ , $f = 0$		1	5		1	5	mA	
			L		2	50		2	50	$\mu A$
			LL		0.1	5		0.1	5	$\mu A$
		Indust'l Temp Range	LL		0.1	10		0.1	10	$\mu A$

**Capacitance<sup>[4]</sup>**

Parameter	Description	Test Conditions	Max.	Unit
$C_{IN}$	Input Capacitance	$T_A = 25^\circ C$ , $f = 1$ MHz, $V_{CC} = 5.0V$	6	pF
$C_{OUT}$	Output Capacitance		8	pF

**AC Test Loads and Waveforms**

**Data Retention Characteristics**

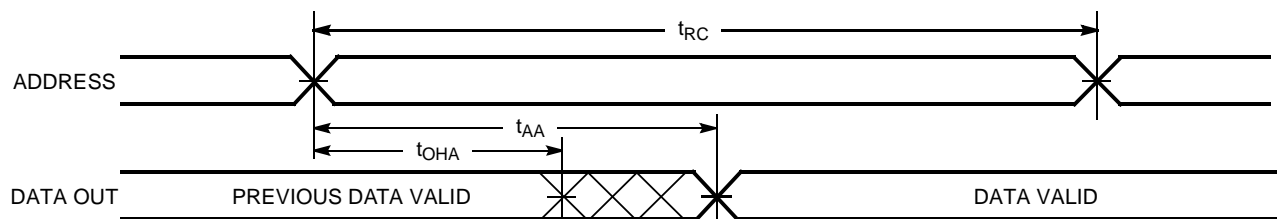
Parameter	Description	Conditions <sup>[5]</sup>	Min.	Typ. <sup>[3]</sup>	Max.	Unit
$V_{DR}$	$V_{CC}$ for Data Retention		2.0			V
$I_{CCDR}$	Data Retention Current	L	$V_{CC} = 3.0V$ , $CE \geq V_{CC} - 0.3V$ , $V_{IN} \geq V_{CC} - 0.3V$ , or $V_{IN} \leq 0.3V$	2	50	$\mu A$
		LL		0.1	5	$\mu A$
		LL Ind'l		0.1	10	$\mu A$
$t_{CDR}^{[4]}$	Chip Deselect to Data Retention Time		0			ns
$t_R^{[4]}$	Operation Recovery Time		$t_{RC}$			ns

**Data Retention Waveform**

**Notes:**

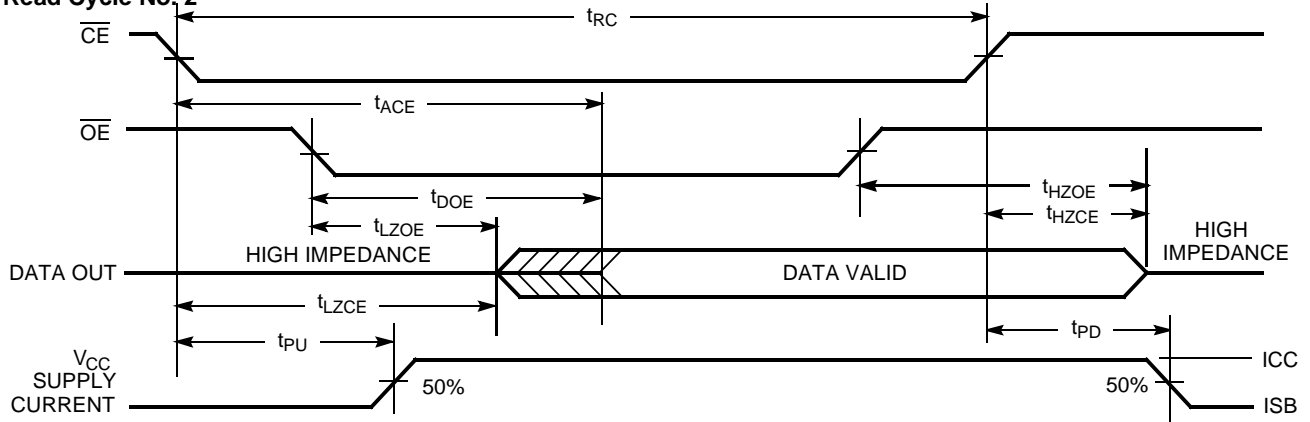
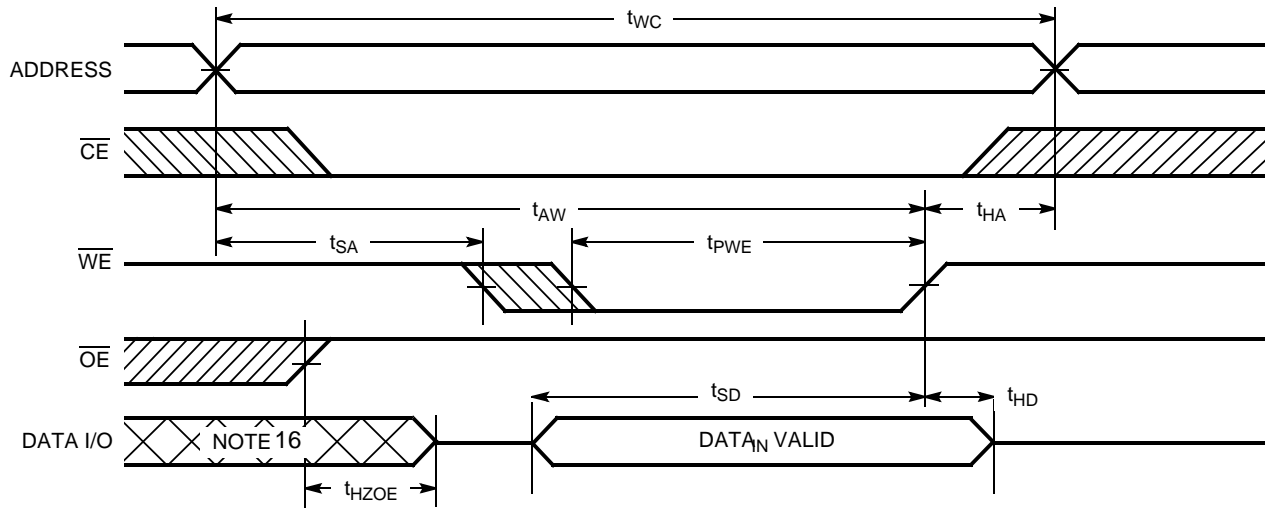
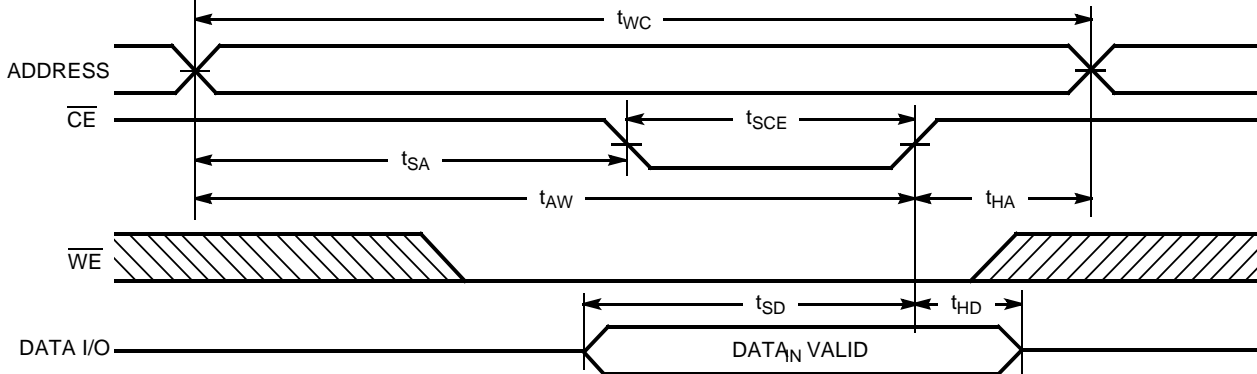
4. Tested initially and after any design or process changes that may affect these parameters.
5. No input may exceed  $V_{CC} + 0.5V$ .

**Switching Characteristics** Over the Operating Range<sup>[6]</sup>

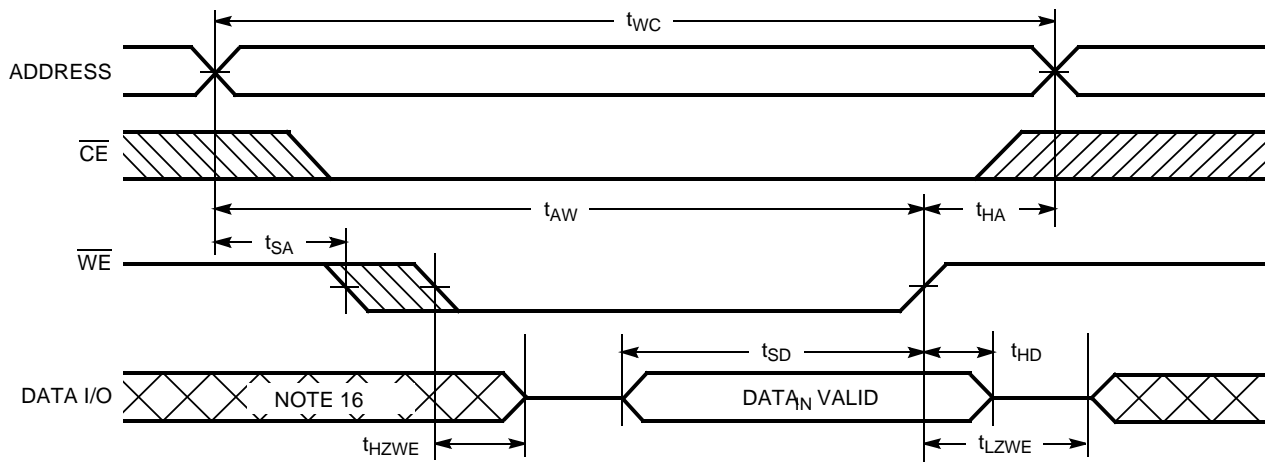
Parameter	Description	CY62256-55		CY62256-70		Unit
		Min.	Max.	Min.	Max.	
<b>Read Cycle</b>						
$t_{RC}$	Read Cycle Time	55		70		ns
$t_{AA}$	Address to Data Valid		55		70	ns
$t_{OHA}$	Data Hold from Address Change	5		5		ns
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid		55		70	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid		25		35	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low-Z <sup>[7]</sup>	5		5		ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High-Z <sup>[7, 8]</sup>		20		25	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low-Z <sup>[7]</sup>	5		5		ns
$t_{HZCE}$	$\overline{CE}$ HIGH to High-Z <sup>[7, 8]</sup>		20		25	ns
$t_{PU}$	$\overline{CE}$ LOW to Power-up	0		0		ns
$t_{PD}$	$\overline{CE}$ HIGH to Power-down		55		70	ns
<b>Write Cycle<sup>[9, 10]</sup></b>						
$t_{WC}$	Write Cycle Time	55		70		ns
$t_{SCE}$	$\overline{CE}$ LOW to Write End	45		60		ns
$t_{AW}$	Address Set-up to Write End	45		60		ns
$t_{HA}$	Address Hold from Write End	0		0		ns
$t_{SA}$	Address Set-up to Write Start	0		0		ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	40		50		ns
$t_{SD}$	Data Set-up to Write End	25		30		ns
$t_{HD}$	Data Hold from Write End	0		0		ns
$t_{HZWE}$	$\overline{WE}$ LOW to High-Z <sup>[7, 8]</sup>		20		25	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low-Z <sup>[7]</sup>	5		5		ns

**Switching Waveforms**
**Read Cycle No. 1<sup>[11, 12]</sup>**

**Notes:**

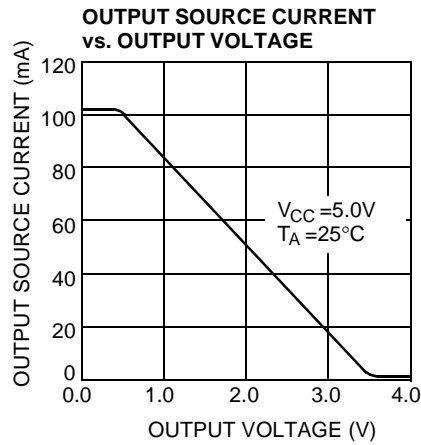
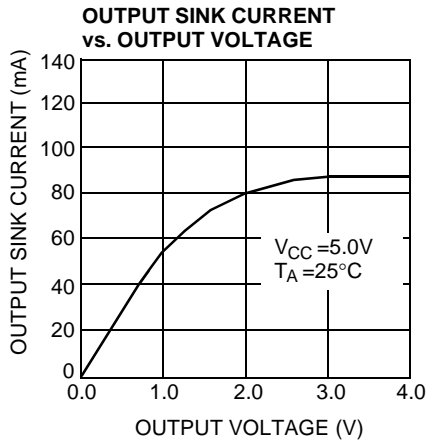
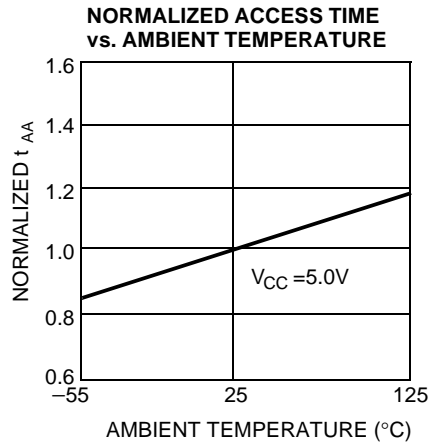
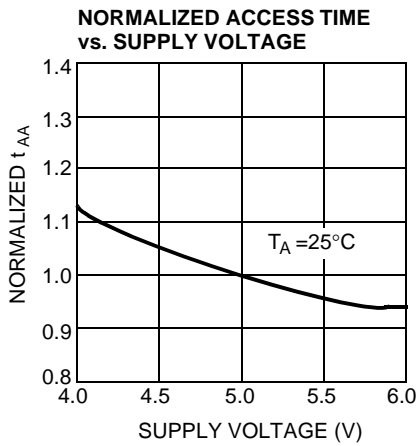
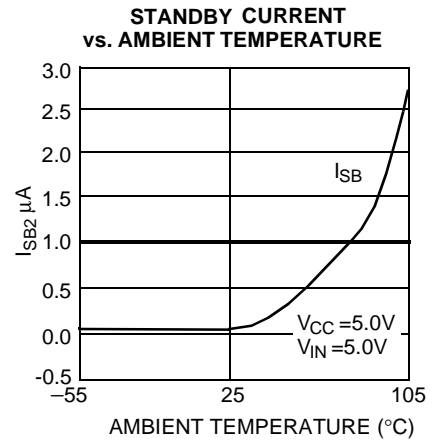
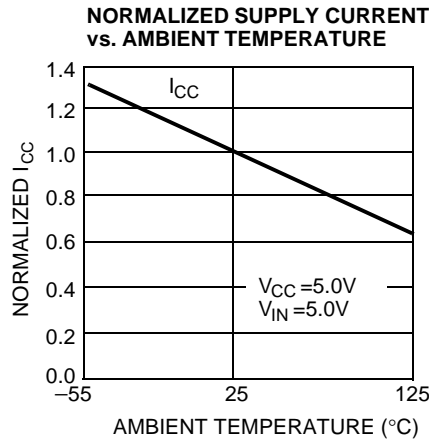
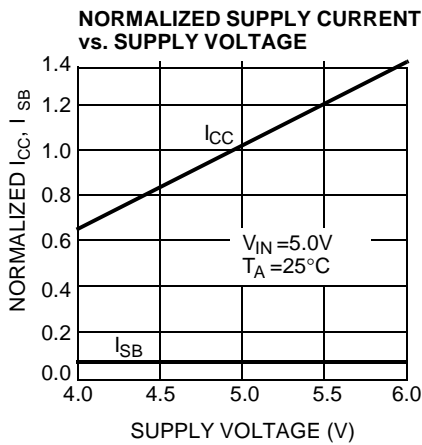
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified  $I_{OL}/I_{OH}$  and 100-pF load capacitance.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
- $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with  $C_L = 5$  pF as in (b) of AC Test Loads. Transition is measured  $\pm 500$  mV from steady-state voltage.
- The internal Write time of the memory is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. Both signals must be LOW to initiate a Write and either signal can terminate a Write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the Write.
- The minimum Write cycle time for Write cycle #3 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) is the sum of  $t_{HZWE}$  and  $t_{SD}$ .
- Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ .
- $\overline{WE}$  is HIGH for Read cycle.

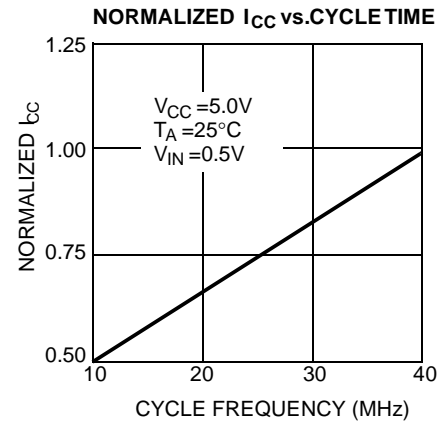
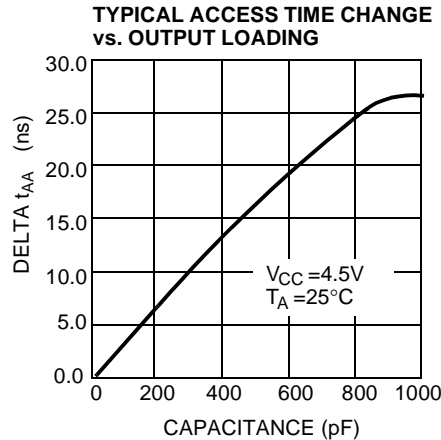
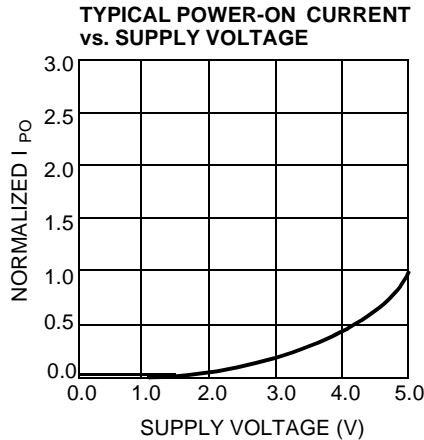
**Switching Waveforms (continued)**
**Read Cycle No. 2** [12, 13]

**Write Cycle No. 1 (WE Controlled)** [9, 14, 15]

**Write Cycle No. 2 ( $\overline{CE}$  Controlled)** [9, 14, 15]

**Notes:**

13. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.
14. Data I/O is high impedance if  $OE = V_{IH}$ .
15. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  HIGH, the output remains in a high-impedance state.

**Switching Waveforms (continued)**
**Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW)** [10, 15]

**Note:**

16. During this period, the I/Os are in output state and input signals should not be applied.

**Typical DC and AC Characteristics**


**Typical DC and AC Characteristics** (continued)

**Truth Table**

CE	WE	OE	Inputs/Outputs	Mode	Power
H	X	X	High-Z	Deselect/Power-down	Standby ( $I_{SB}$ )
L	H	L	Data Out	Read	Active ( $I_{CC}$ )
L	L	X	Data In	Write	Active ( $I_{CC}$ )
L	H	H	High-Z	Deselect, Output Disabled	Active ( $I_{CC}$ )

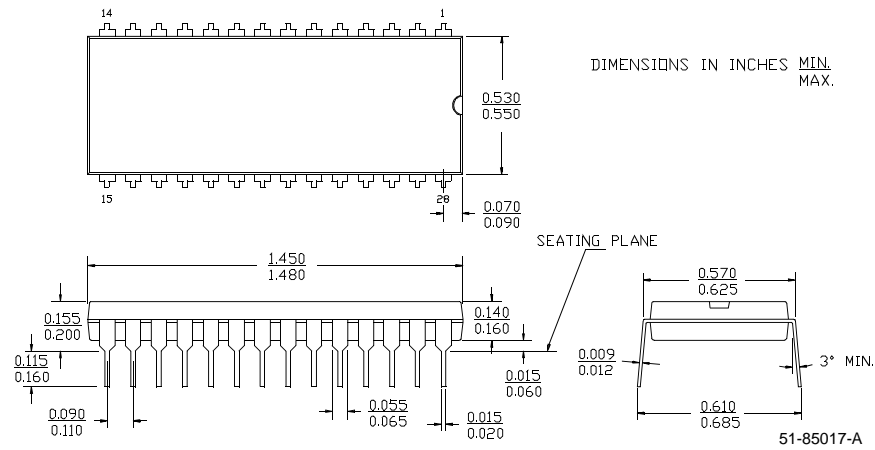
**Ordering Information**

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62256LL-55SNI	SN28	28-lead (300-Mil Narrow Body) Narrow SOIC	Industrial
	CY62256LL-55ZI	Z28	28-lead Thin Small Outline Package	
70	CY62256-70SNC	SN28	28-lead (300-Mil Narrow Body) Narrow SOIC	Commercial
	CY62256L-70SNC			
	CY62256LL-70SNC			
	CY62256L-70SNI			
	CY62256LL-70SNI			
	CY62256LL-70ZC	Z28	28-lead Thin Small Outline Package	Commercial
	CY62256LL-70ZI	Z28		Industrial
	CY62256-70PC	P15	28-lead (600-Mil) Molded DIP	Commercial
	CY62256L-70PC	P15		
	CY62256LL-70PC	P15		
CY62256LL-70ZRI	ZR28	28-lead Reverse Thin Small Outline Package	Industrial	

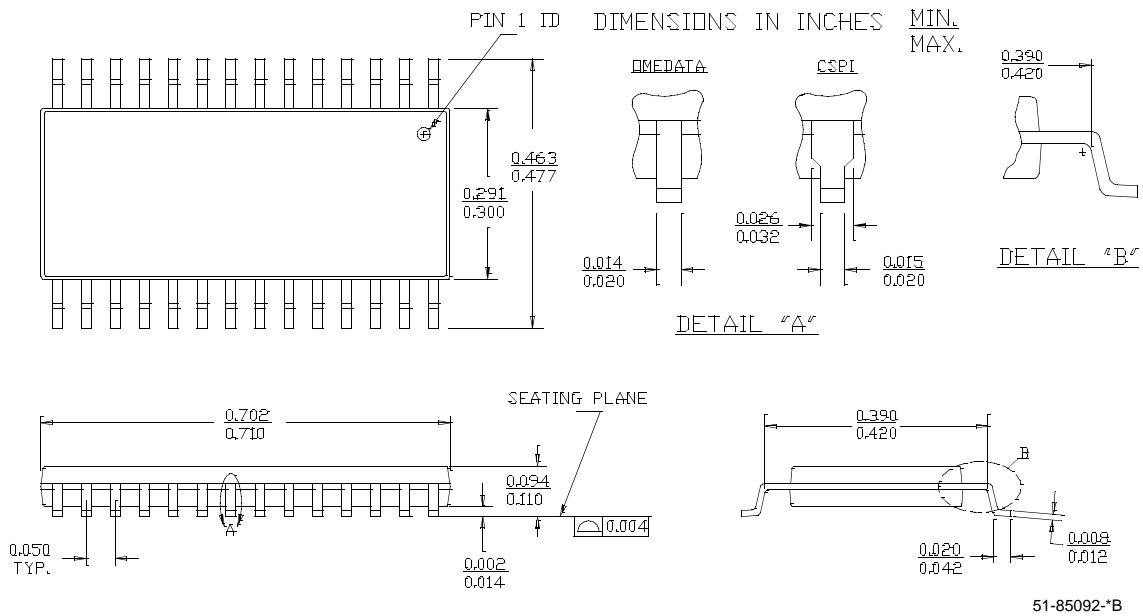


Package Diagrams

28-lead (600-mil) Molded DIP P15



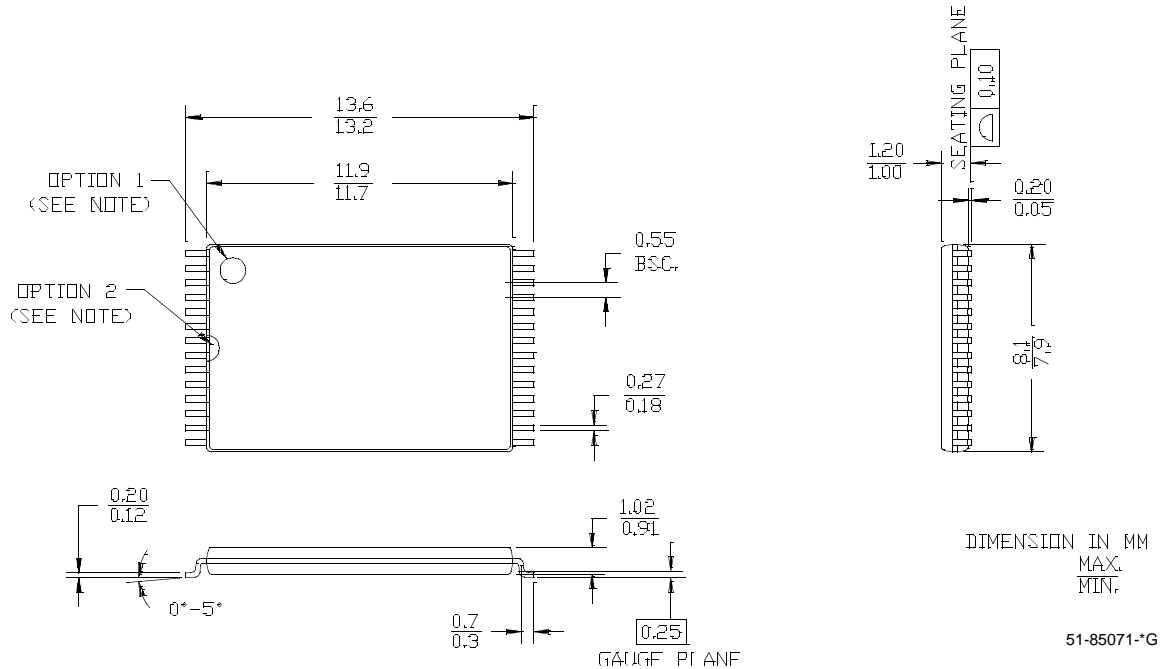
28-lead (300-mil) SNC (Narrow Body) SN28



Package Diagrams (continued)

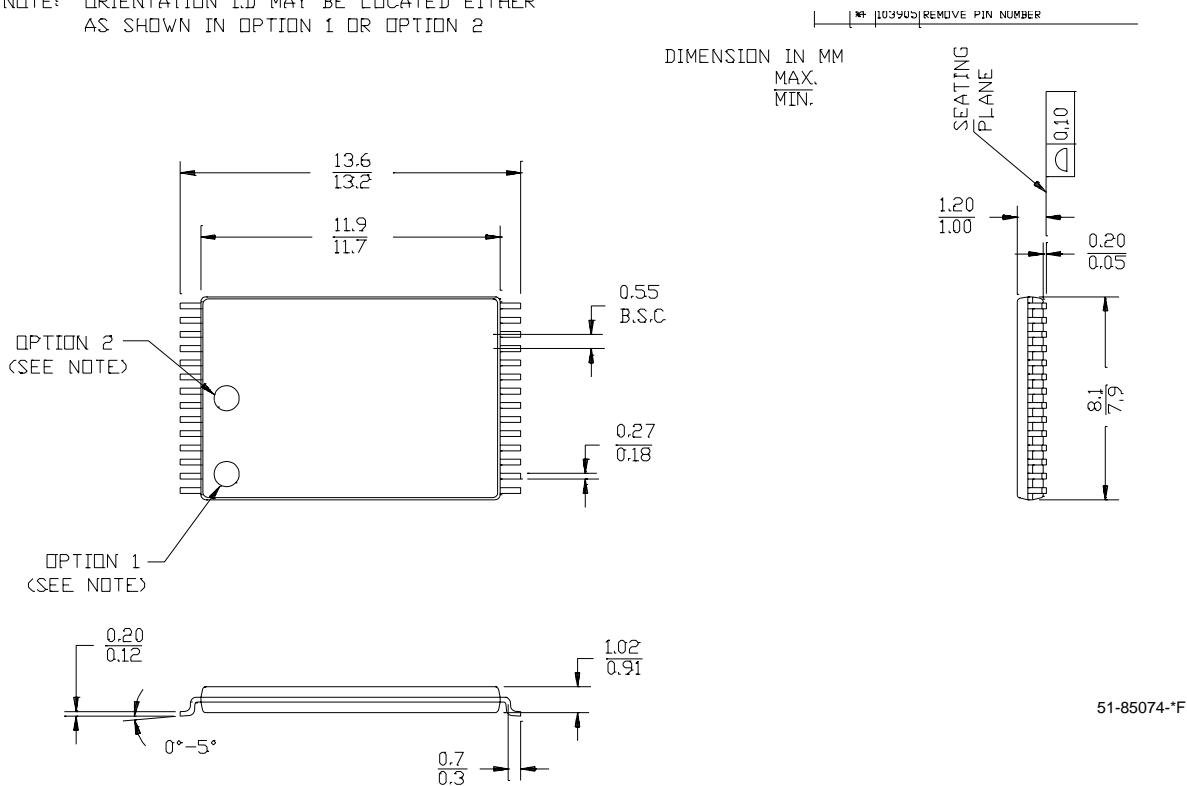
**28-lead Thin Small Outline Package Type 1 (8 x 13.4 mm) Z28**

NOTE: ORIENTATION I.D. MAY BE LOCATED EITHER AS SHOWN IN OPTION 1 OR OPTION 2



**28-lead Reverse Type 1 Thin Small Outline Package (8 x 13.4 mm) ZR28**

NOTE: ORIENTATION I.D. MAY BE LOCATED EITHER AS SHOWN IN OPTION 1 OR OPTION 2



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Document Title: CY62256 256K (32K x 8) Static RAM				
Document Number: 38-05248				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	113454	03/06/02	MGN	Change from Spec number: 38-00455 to 38-05248 Remove obsolete parts from ordering info, standardize format
*A	115227	05/23/02	GBI	Changed SN Package Diagram
*B	116506	09/04/02	GBI	Added footnote 1. Corrected package description in Ordering Information table